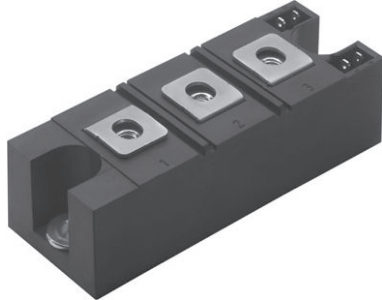





**Thyristor/Diode and Thyristor/Thyristor, 135 A to 160 A
(New INT-A-PAK Power Modules)**



New INT-A-PAK

PRODUCT SUMMARY	
$I_{T(AV)}$	135 A to 160 A
Type	Modules - Thyristor, Standard
Package	INT-A-PAK
Circuit	Two SCRs doubler circuit, SCR/diode doubler circuit, positive control, SCR/diode doubler circuit, negative control

FEATURES

- High voltage
- Electrically isolated by DBC ceramic (Al_2O_3)
- 3500 V_{RMS} isolating voltage
- Industrial standard package
- High surge capability
- Glass passivated chips
- Modules uses high voltage power thyristor/diodes in three basic configurations
- Simple mounting
- UL approved file E78996 
- Designed and qualified for multiple level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



**RoHS
COMPLIANT**

APPLICATIONS

- DC motor control and drives
- Battery charges
- Welders
- Power converters
- Lighting control
- Heat and temperature control

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VSK.136..	VSK.142..	VSK.162..	UNITS
$I_{T(AV)}$	85 °C	135	140	160	A
$I_{T(RMS)}$		300	310	355	A
I_{TSM}	50 Hz	3200	4500	4870	
	60 Hz	3360	4712	5100	
I^2t	50 Hz	51.5	102	119	kA ² s
	60 Hz	47	92.5	108	
$I^2\sqrt{t}$		515.5	1013	1190	kA ² √s
V_{RRM}	Range	400 to 1600	400 to 1600	400 to 1600	V
T_J	Range	-40 to 125			°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM}/V_{DSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-VSK.136 VS-VSK.142 VS-VSK.162	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	



ON-STATE CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS		VSK.136	VSK.142	VSK.162	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		135	140	160	A
				85	85	85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	As AC switch		300	310	355	A
Maximum peak, one-cycle on-state, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reappplied	3200	4500	4870	
		t = 8.3 ms		3360	4712	5100	
		t = 10 ms	100 % V_{RRM} reappplied	2700	3785	4100	
		t = 8.3 ms		2800	3963	4300	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied	51.5	102	119	kA ² s
		t = 8.3 ms		47	92.5	108	
		t = 10 ms	100 % V_{RRM} reappplied	36.5	71.6	84	
		t = 8.3 ms		33.3	65.4	76.7	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reappplied		515.5	1013	1190	kA ² √s
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$, T_J maximum)		0.86	0.83	0.8	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > $\pi \times I_{T(AV)}$, T_J maximum)		1.05	1	0.98	
Low level value on-state slope resistance	r_{t1}	(16.7 % $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$, T_J maximum)		2.02	1.78	1.67	mΩ
High level value on-state slope resistance	r_{t2}	(I > $\pi \times I_{T(AV)}$, T_J maximum)		1.65	1.43	1.38	
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$, $T_J = 25\text{ °C}$, 180° conduction		1.57	1.55	1.54	V
Maximum forward voltage drop	V_{FM}	$I_{TM} = \pi \times I_{T(AV)}$, $T_J = 25\text{ °C}$, 180° conduction		1.57	1.55	1.54	V
Maximum holding current	I_H	Anode supply = 6 V initial $I_T = 30\text{ A}$, $T_J = 25\text{ °C}$		200			mA
Maximum latching current	I_L	Anode supply = 6 V resistive load = 1 Ω Gate pulse: 10 V, 100 μs, $T_J = 25\text{ °C}$		400			

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical delay time	t_{gd}	$T_J = 25\text{ °C}$	Gate current = 1 A, $di_g/dt = 1\text{ A}/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$	1	μs
Typical rise time	t_{gr}			2	
Typical turn-off time	t_q	$I_{TM} = 300\text{ A}$, - $di/dt = 15\text{ A}/\mu\text{s}$; $T_J = T_J$ maximum $V_R = 50\text{ V}$; $dV/dt = 20\text{ V}/\mu\text{s}$; gate 0 V, 100 Ω		50 to 200	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = 125\text{ °C}$		50	mA
RMS insulation voltage	V_{INS}	50 Hz, circuit to base, all terminals shorted, t = 1 s		3500	V
Critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, exponential to 67 % rated V_{DRM}		1000	V/μs



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}	$t_p \leq 5 \text{ ms}$, $T_J = T_J \text{ maximum}$		12	W
Maximum average gate power	$P_{G(AV)}$	$f = 50 \text{ Hz}$, $T_J = T_J \text{ maximum}$		3	
Maximum peak gate current	I_{GM}	$t_p \leq 5 \text{ ms}$, $T_J = T_J \text{ maximum}$		3	A
Maximum peak negative gate voltage	$-V_{GT}$			10	V
Maximum required DC gate voltage to trigger	V_{GT}	$T_J = -40 \text{ }^\circ\text{C}$	Anode supply = 6 V, resistive load; $R_a = 1 \text{ } \Omega$	4	
		$T_J = 25 \text{ }^\circ\text{C}$		2.5	
		$T_J = T_J \text{ maximum}$		1.7	
Maximum required DC gate current to trigger	I_{GT}	$T_J = -40 \text{ }^\circ\text{C}$		270	mA
		$T_J = 25 \text{ }^\circ\text{C}$		150	
		$T_J = T_J \text{ maximum}$		80	
Maximum gate voltage that will not trigger	V_{GD}	$T_J = T_J \text{ maximum}$, rated V_{DRM} applied		0.3	V
Maximum gate current that will not trigger	I_{GD}			10	mA
Maximum rate of rise of turned-on current	di/dt	$T_J = T_J \text{ maximum}$, $I_{TM} = 400 \text{ A}$ rated V_{DRM} applied		300	A/ μs

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VSK.136	VSK.142	VSK.162	UNITS
Maximum junction operating temperature range	T_J		-40 to 125			$^\circ\text{C}$
Maximum storage temperature range	T_{Stg}		-40 to 150			
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	0.18	0.18	0.16	K/W
Maximum thermal resistance, case to heatsink per module	R_{thCS}	Mounting surface, smooth, flat and greased	0.05			
Mounting torque $\pm 10 \%$		IAP to heatsink busbar to IAP	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.			Nm
Approximate weight						4 to 6
			200			g
Case style						oz.
			INT-A-PAK			

ΔR CONDUCTION PER JUNCTION											
DEVICES	SINUSOIDAL CONDUCTION AT T_J MAXIMUM					RECTANGULAR CONDUCTION AT T_J MAXIMUM					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSK.136	0.007	0.01	0.013	0.0155	0.017	0.009	0.012	0.014	0.015	0.017	K/W
VSK.142	0.0019	0.0019	0.0020	0.0020	0.0021	0.0018	0.0022	0.0023	0.0023	0.0020	
VSK.162	0.0030	0.0031	0.0032	0.0033	0.0034	0.0029	0.0036	0.0039	0.0041	0.0040	

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

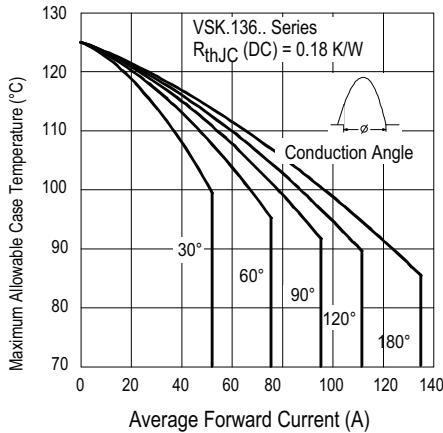


Fig. 1 - Current Ratings Characteristics

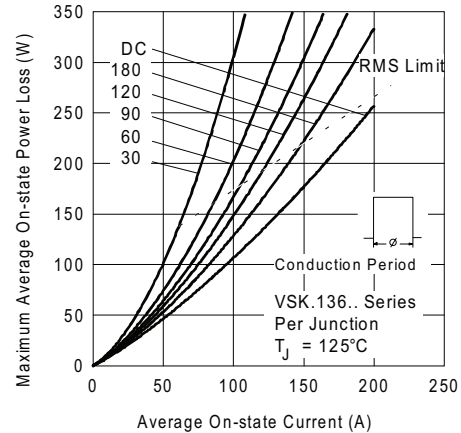


Fig. 4 - On-State Power Loss Characteristics

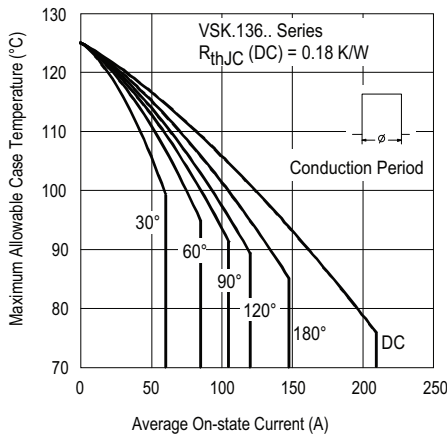


Fig. 2 - Current Ratings Characteristics

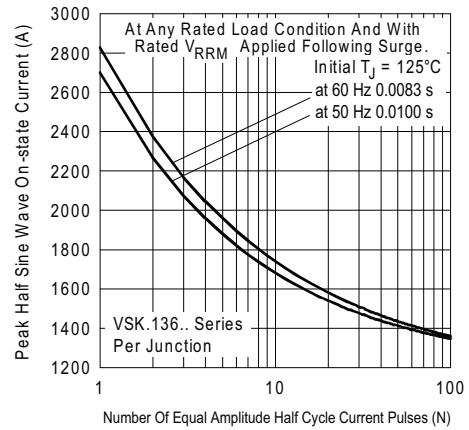


Fig. 5 - Maximum Non-Repetitive Surge Current

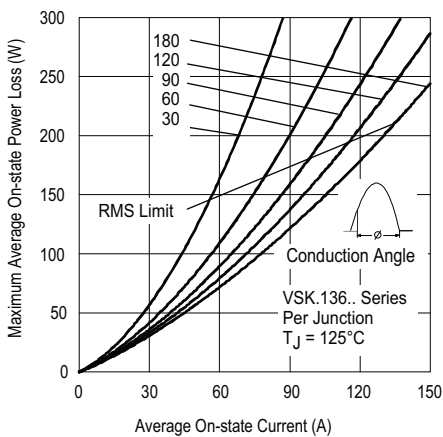


Fig. 3 - On-State Power Loss Characteristics

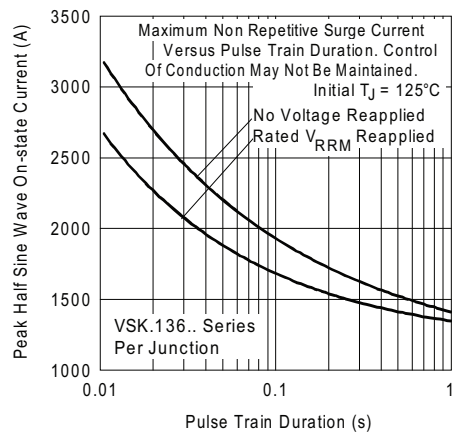


Fig. 6 - Maximum Non-Repetitive Surge Current

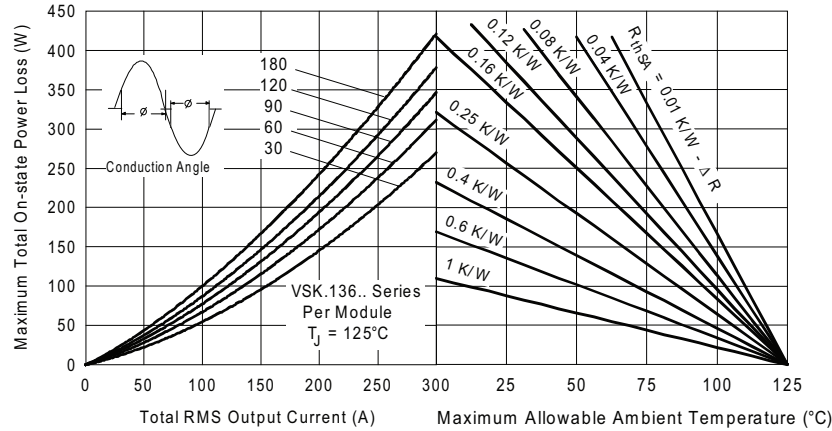


Fig. 7 - On-State Power Loss Characteristics

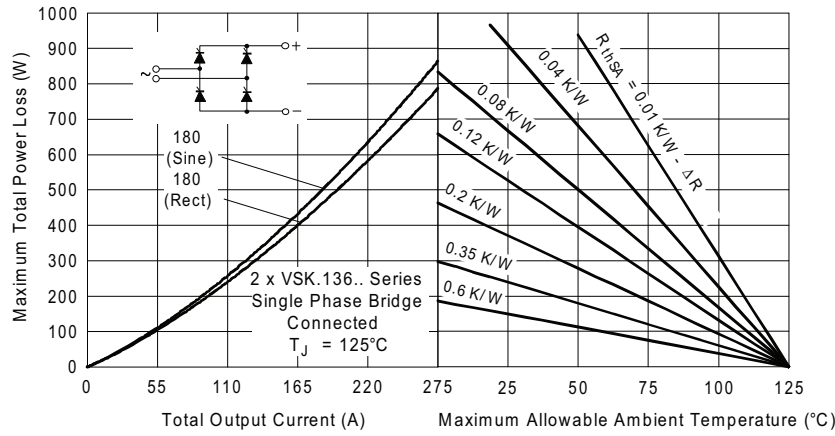


Fig. 8 - On-State Power Loss Characteristics

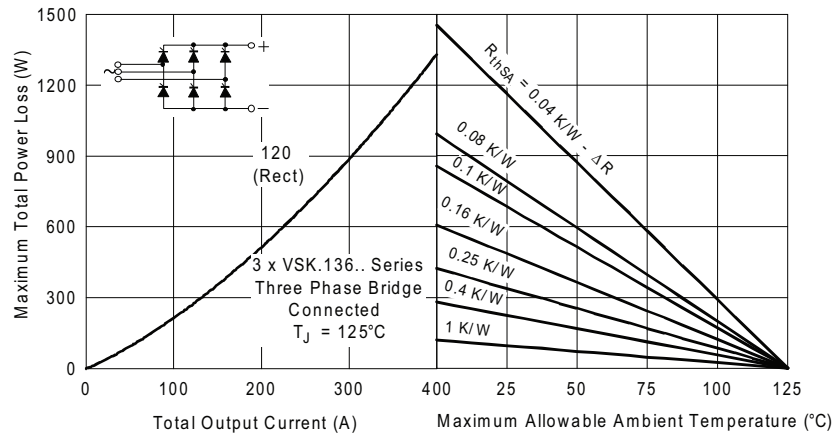


Fig. 9 - On-State Power Loss Characteristics

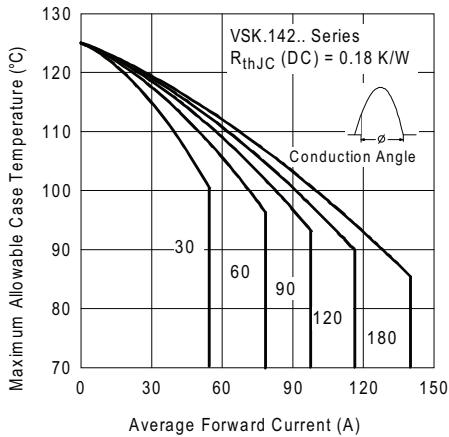


Fig. 10 - Current Ratings Characteristics

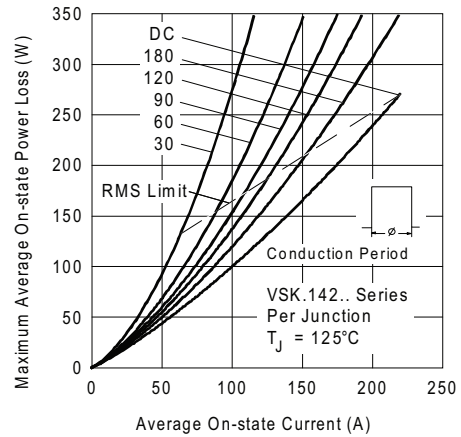


Fig. 13 - On-State Power Loss Characteristics

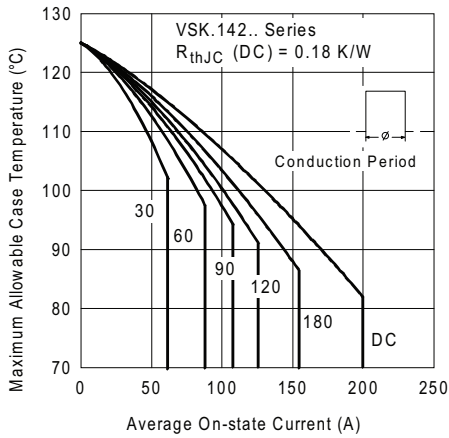


Fig. 11 - Current Ratings Characteristics

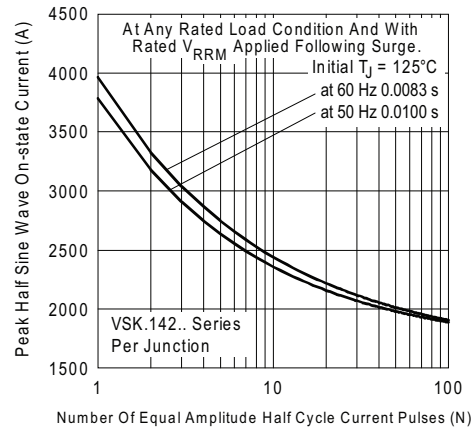


Fig. 14 - Maximum Non-Repetitive Surge Current

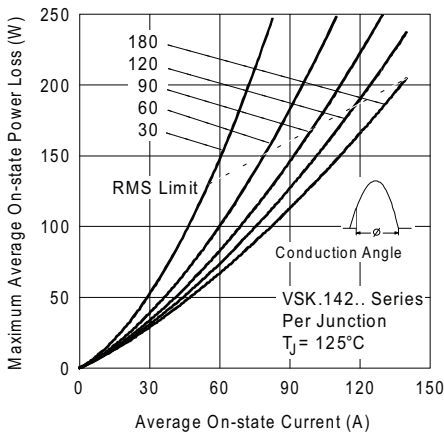


Fig. 12 - On-State Power Loss Characteristics

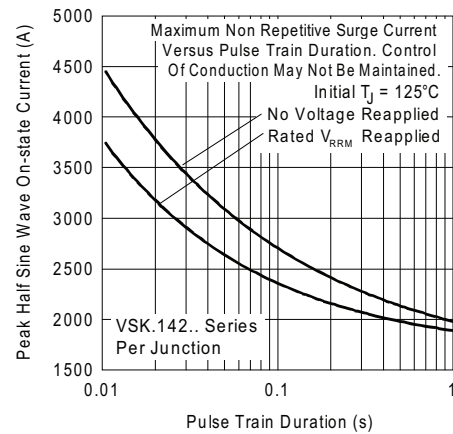


Fig. 15 - Maximum Non-Repetitive Surge Current

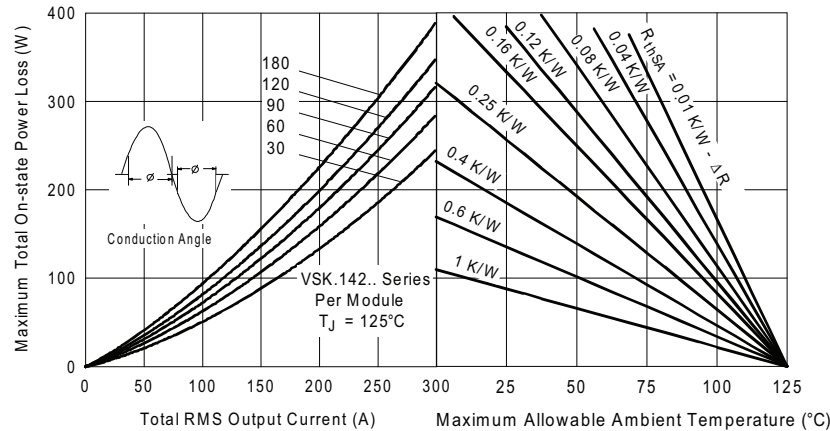


Fig. 16 - On-State Power Loss Characteristics

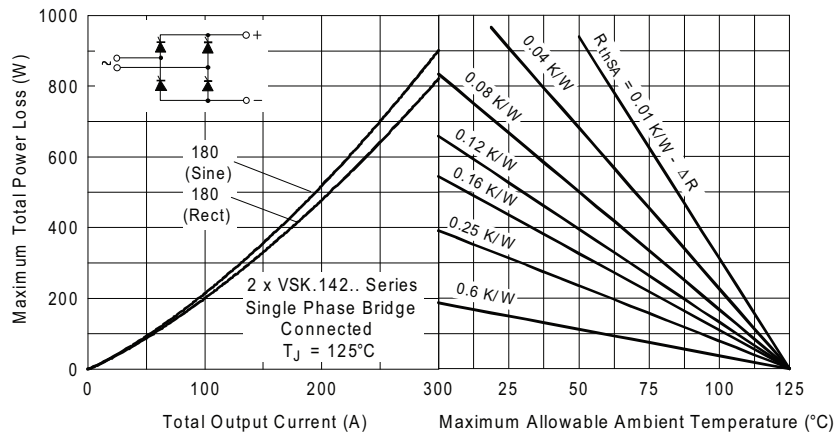


Fig. 17 - On-State Power Loss Characteristics

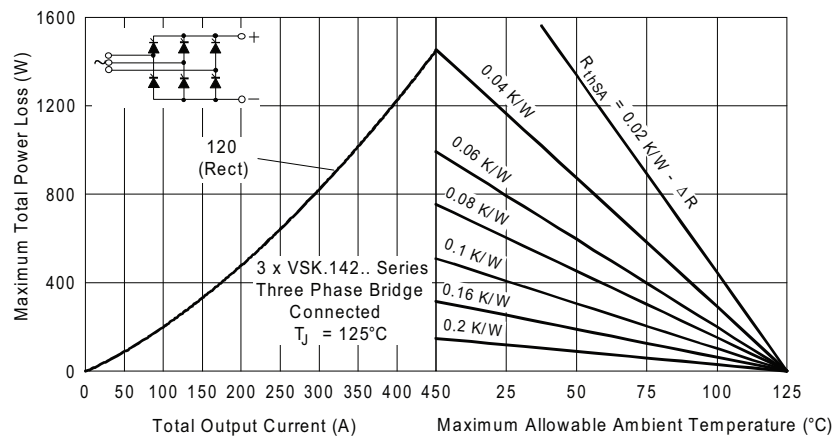


Fig. 18 - On-State Power Loss Characteristics

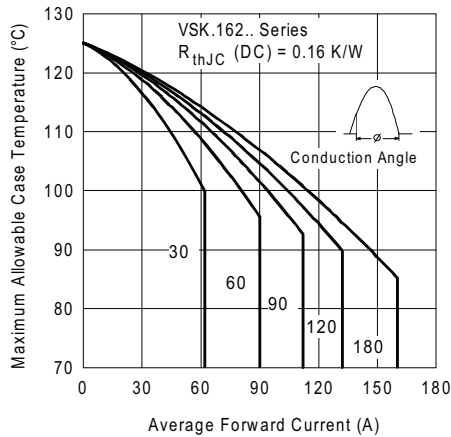


Fig. 19 - Current Ratings Characteristics

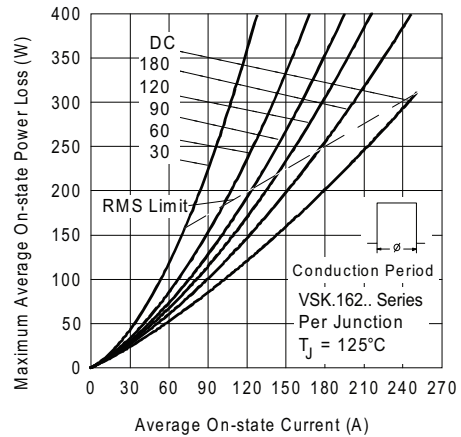


Fig. 22 - On-State Power Loss Characteristics

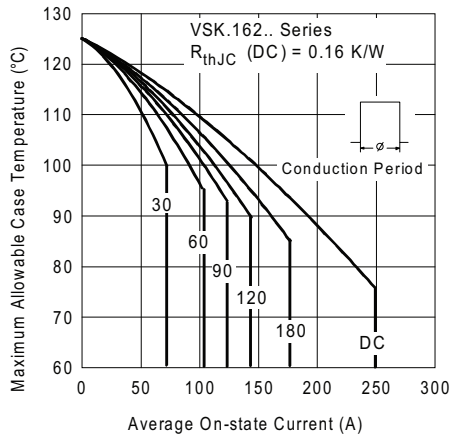


Fig. 20 - Current Ratings Characteristics

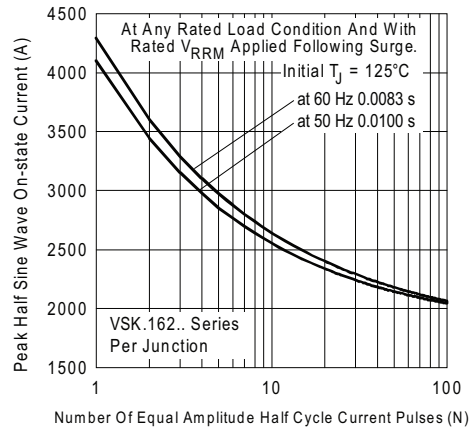


Fig. 23 - Maximum Non-Repetitive Surge Current

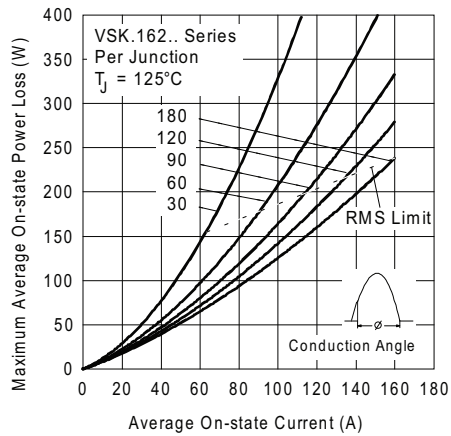


Fig. 21 - On-State Power Loss Characteristics

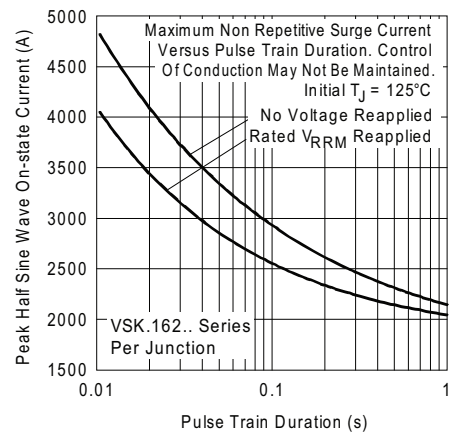


Fig. 24 - Maximum Non-Repetitive Surge Current

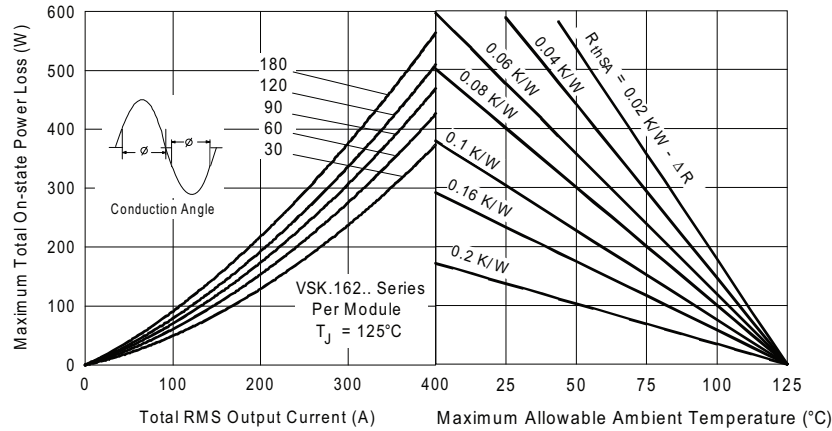


Fig. 25 - On-State Power Loss Characteristics

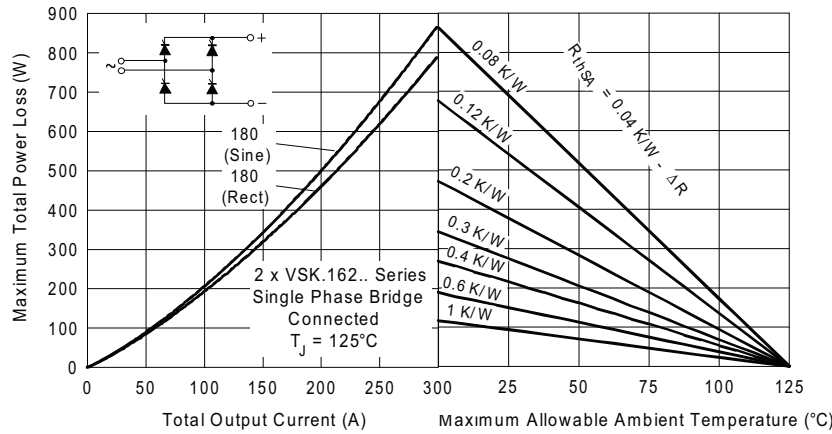


Fig. 26 - On-State Power Loss Characteristics

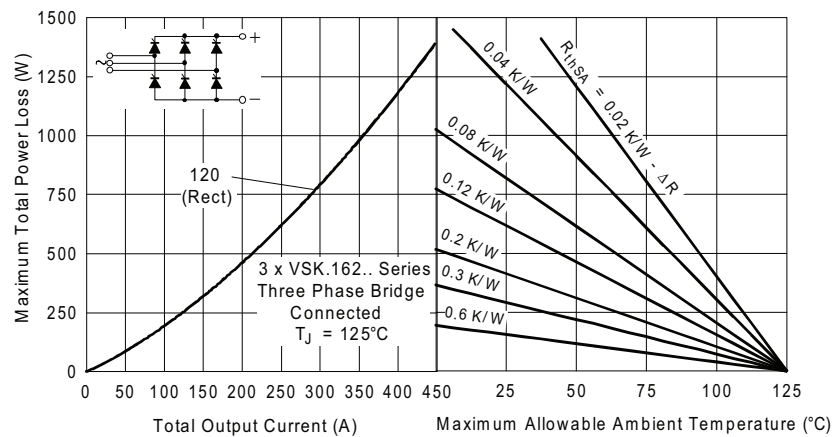


Fig. 27 - On-State Power Loss Characteristics

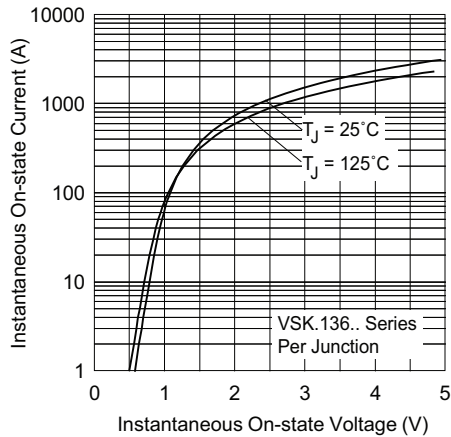


Fig. 28 - On-State Voltage Drop Characteristics

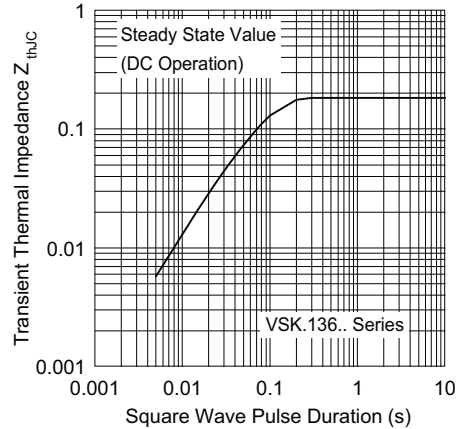


Fig. 31 - Thermal Impedance Z_{thJC} Characteristics

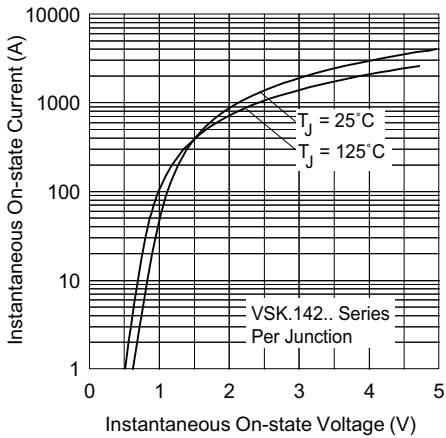


Fig. 29 - On-State Voltage Drop Characteristics

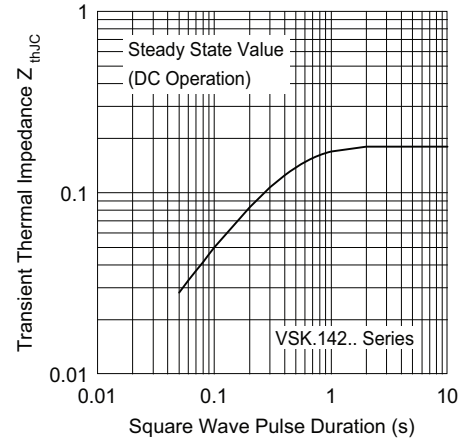


Fig. 32 - Thermal Impedance Z_{thJC} Characteristics

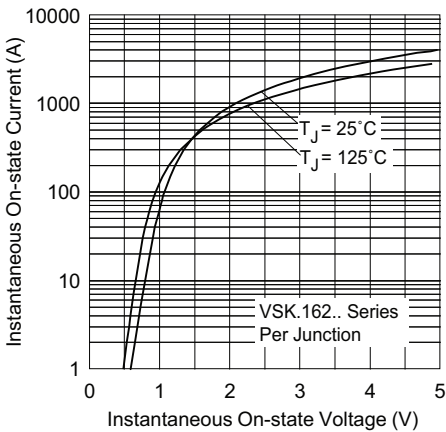


Fig. 30 - On-State Voltage Drop Characteristics

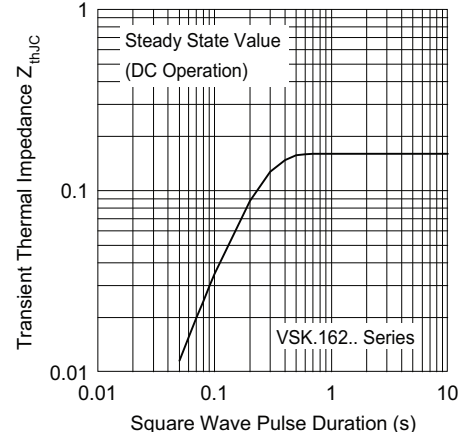


Fig. 33 - Thermal Impedance Z_{thJC} Characteristics

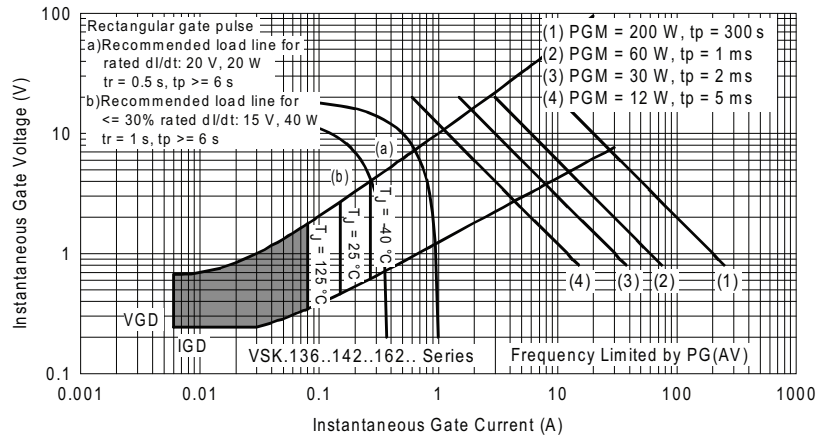


Fig. 34 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-VS	KT	162	16	PbF
	①	②	③	④	⑤
	1	-	Vishay Semiconductors product		
	2	-	Circuit configuration		
	3	-	Current rating: $I_{T(AV)}$		
	4	-	Voltage code x 100 = V_{RRM}		
	5	-	PbF = Lead (Pb)-free		

Note

- To order the optional hardware go to www.vishay.com/doc?95172

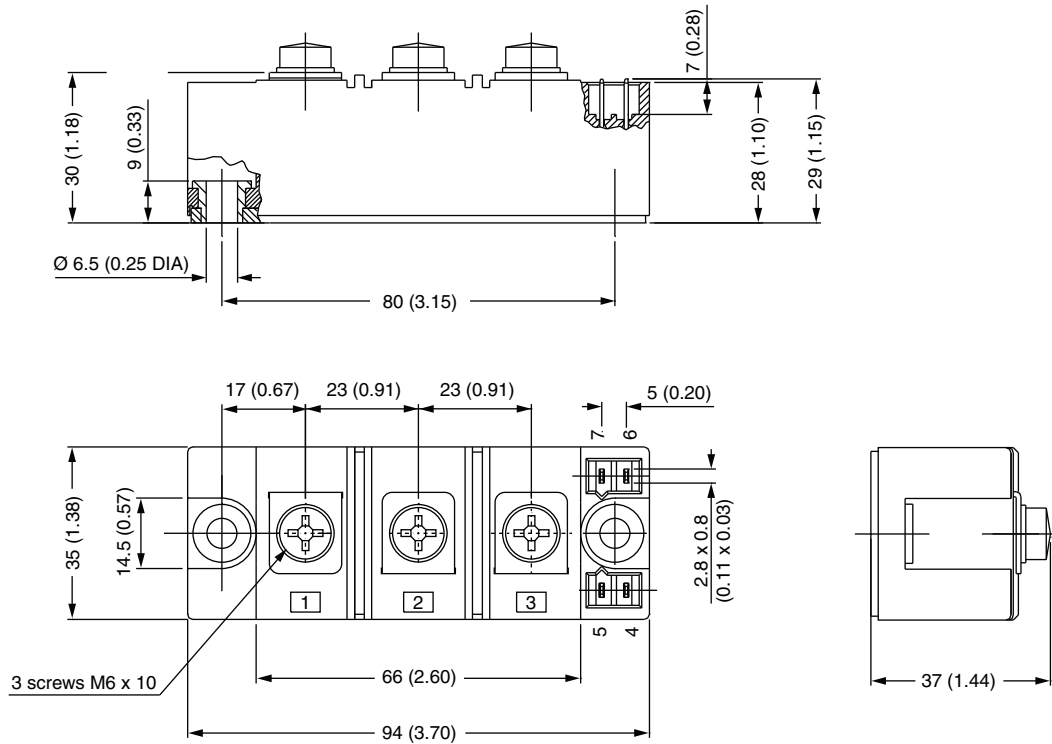


CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	T	
SCR/diode doubler circuit, positive control	H	
SCR/diode doubler circuit, negative control	L	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95067

INT-A-PAK IGBT/Thyristor

DIMENSIONS in millimeters (inches)





Disclaimer

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